IN THE CLAIMS

Claims 1 - 16 (Cancelled)

17. (Currently Amended) An integrated circuit (IC) comprising:

an oxide layer;

an adhesion layer formed on a surface of said oxide layer by treating said surface of said oxide layer with a gas; and

a first passivation layer formed on said adhesion layer, said first passivation layer and said adhesion layer including at least one common chemical element.

18. (Original) The integrated circuit of claim 17 further comprising a second passivation layer formed upon said first passivation layer.

19. (Previously Presented) The integrated circuit of claim 17 wherein said oxide layer includes silicon dioxide (SiO_2).

20. (Original) The integrated circuit of claim 17 wherein said adhesion layer includes silicon oxynitride.

21. (Original) The integrated circuit of claim 17 wherein said first passivation layer includes silicon nitride (Si_3N_4).

22. (Original) The integrated circuit of claim 18 wherein said second passivation layer includes polyimide.

23. (Currently Amended) An integrated circuit comprising in a three layer stack:

a silicon dioxide insulating layer;

a silicon oxynitride adhesion layer formed on a surface of said silicon dioxide insulating layer by treating said surface of said silicon dioxide insulating layer with a gas; and

a silicon nitride hard passivation layer formed directly on a surface of said silicon oxynitride adhesion layer.

24. (Original) The integrated circuit passivation layer of claim 23 further comprising a photodefinable polyimide soft passivation layer formed on said silicon nitride hard passivation layer.

Please add the following new claims:

-- 25. (New) The integrated circuit of claim 17, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH_3), oxygen and argon (Ar) and ozone (O_3) and argon.

26. (New) The integrated circuit of claim 23, wherein said gas includes one of oxygen and nitrogen (N), oxygen and ammonia (NH_3), oxygen and argon (Ar) and ozone (O_3) and argon. --